

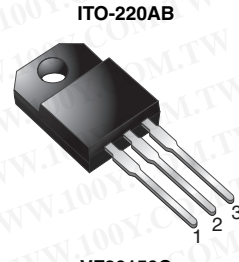
Dual High Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.59\text{ V}$ at $I_F = 5\text{ A}$

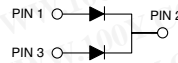
TMBS®



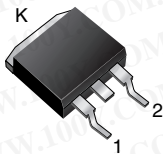
V20150C



VF20150C



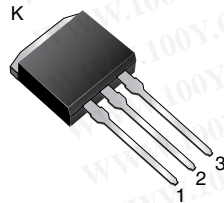
TO-263AB



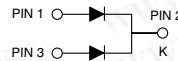
VB20150C



TO-262AA



VI20150C



FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB and TO-262AA package)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB, and TO-262AA

Molding compound meets UL 94 V-0 flammability rating
Base P/N-E3 - RoHS-compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_{RRM}	150 V
I_{FSM}	120 A
V_F at $I_F = 10\text{ A}$	0.69 V
T_J max.	150 °C
Package	TO-220AB, ITO-220AB, TO-263AB, TO-262AA
Diode variations	Dual common cathode

勝特力材料 886-3-5753170
 胜特力电子(上海) 86-21-34970699
 胜特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

MAXIMUM RATINGS ($T_A = 25\text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	V20150C	VF20150C	VB20150C	VI20150C	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}			150		V
Maximum average forward rectified current	$I_{F(AV)}$	per device		20		A
(fig. 1)		per diode		10		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}			120		A
Non-repetitive avalanche energy at $T_J = 25\text{ °C}$, $L = 60\text{ mH}$ per diode	E_{AS}			70		mJ
Peak repetitive reverse current at $t_p = 2\text{ }\mu\text{s}$, 1 kHz, $T_J = 38\text{ °C} \pm 2\text{ °C}$ per diode	I_{RRM}			0.5		A
Voltage rate of change (rated V_F)	dV/dt			10 000		V/ μs
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1\text{ min}$	V_{AC}			1500		V
Operating junction and storage temperature range	T_J, T_{STG}			-55 to +150		°C



ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I _R = 1.0 mA	T _A = 25 °C	V _{BR}	150 (minimum)	-	V
Instantaneous forward voltage per diode ⁽¹⁾	I _F = 5 A	T _A = 25 °C	V _F	0.79	-	V
	I _F = 10 A			1.05	1.20	
	I _F = 5 A	T _A = 125 °C		0.59	-	
	I _F = 10 A			0.69	0.75	
Reverse current per diode ⁽²⁾	V _R = 100 V	T _A = 25 °C	I _R	1.3	-	μA
		T _A = 125 °C		1.2	-	mA
	V _R = 150 V	T _A = 25 °C		-	150	μA
		T _A = 125 °C		3	15	mA

Notes

- (1) Pulse test: 300 μs pulse width, 1 % duty cycle
- (2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	V20150C	VF20150C	VB20150C	VI20150C	UNIT
Typical thermal resistance per diode	R _{θJC}	2.8	5.0	2.8	2.8	°C/W

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	V20150C-E3/4W	1.88	4W	50/tube	Tube
ITO-220AB	VF20150C-E3/4W	1.75	4W	50/tube	Tube
TO-263AB	VB20150C-E3/4W	1.39	4W	50/tube	Tube
TO-263AB	VB20150C-E3/8W	1.39	8W	800/reel	Tape and reel
TO-262AA	VI20150C-E3/4W	1.45	4W	50/tube	Tube

RATINGS AND CHARACTERISTICS CURVES (T_A = 25 °C unless otherwise noted)

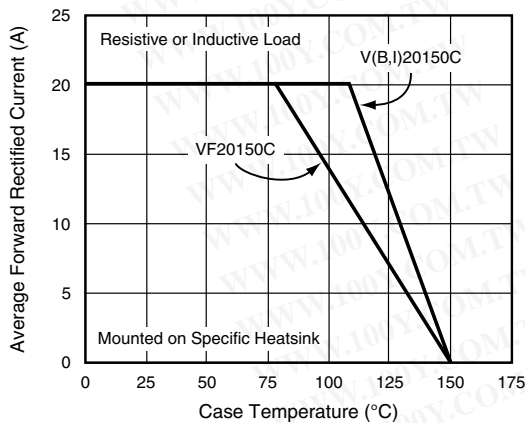


Fig. 1 - Maximum Forward Current Derating Curve

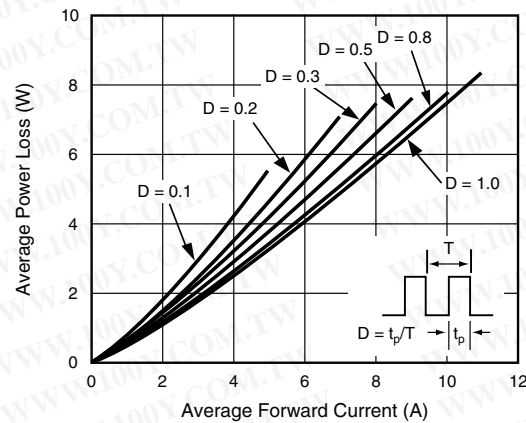


Fig. 2 - Forward Power Loss Characteristics Per Diode

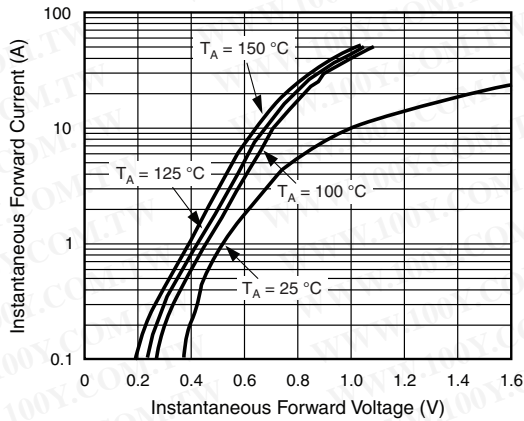


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

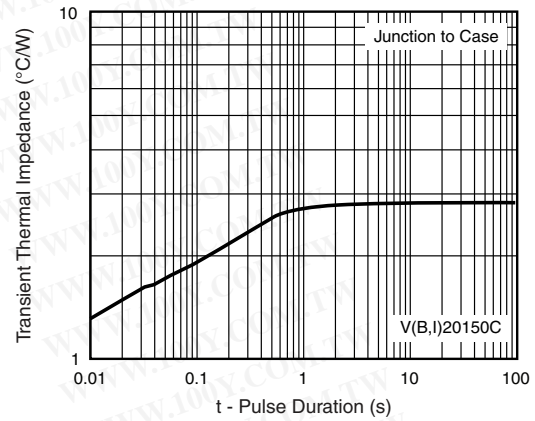


Fig. 6 - Typical Transient Thermal Impedance Per Diode

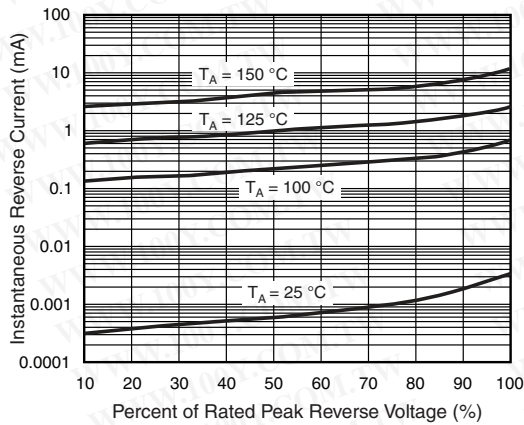


Fig. 4 - Typical Reverse Characteristics Per Diode

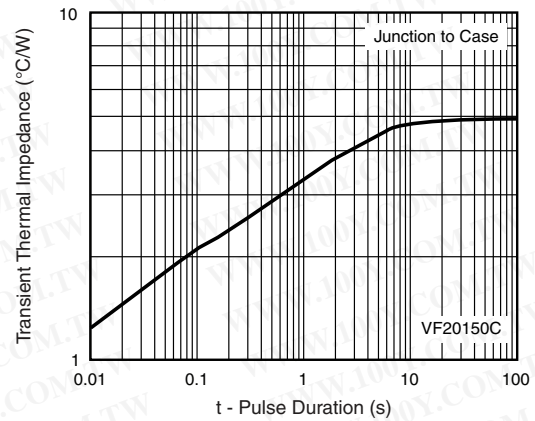


Fig. 7 - Typical Transient Thermal Impedance Per Diode

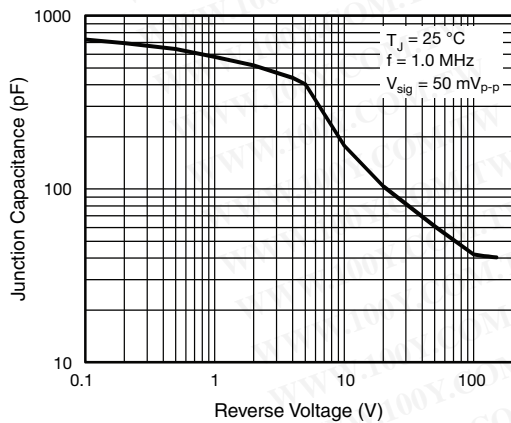


Fig. 5 - Typical Junction Capacitance



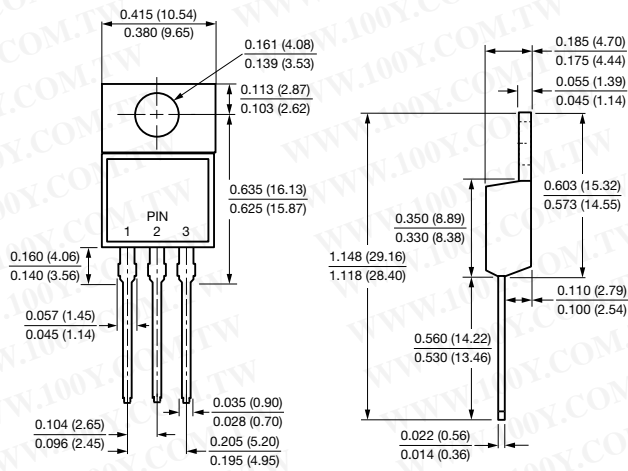
V20150C-E3, VF20150C-E3, VB20150C-E3, VI20150C-E3

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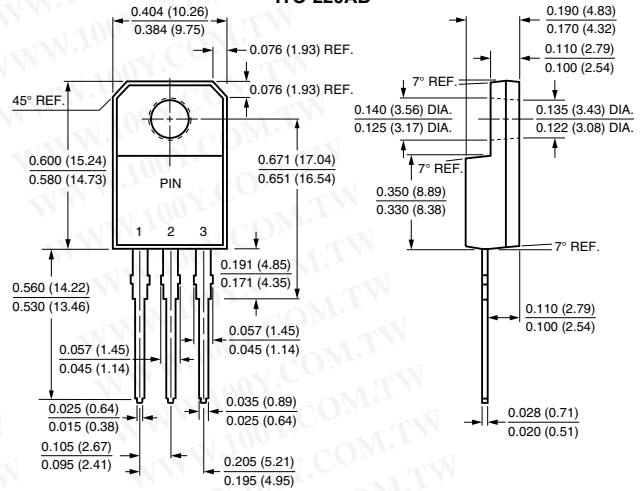
Vishay General Semiconductor

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

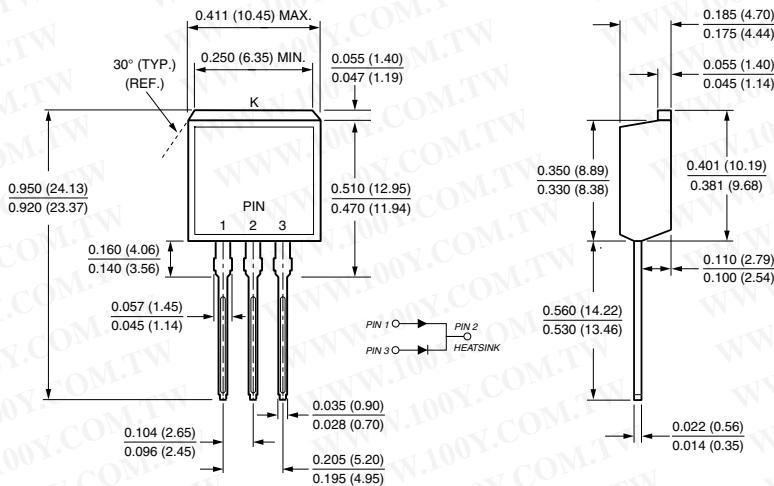
TO-220AB



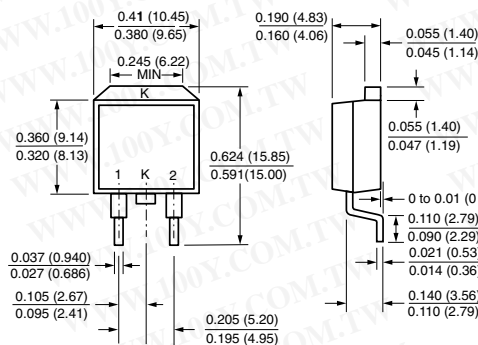
ITO-220AB



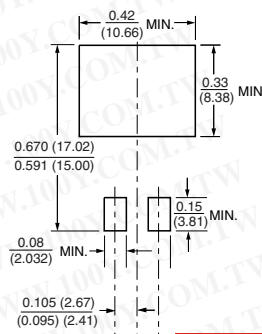
TO-262AA



TO-263AB



Mounting Pad Layout



勝特力材料 886-3-5753170
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 勝特力电子(深圳) 86-755-83298787
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